# NSN 5961-00-137-4066

Semiconductor Device Set - Page 1 of 2

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**Inclosure Material:**

Metal all transistor

**Overall Length:**

0.190 inches all transistor

**Terminal Length:**

0.500 inches all transistor

**Overall Diameter:**

0.219 inches all transistor

**Internal Configuration:**

Field effect all transistor

**Channel Polarity And Control Type (non-core):**

N-channel insulated gate type all transistor

**Component Function Relationship:**

Matched

**Component Name And Quantity:**

2 transistor

**Mounting Method:**

Terminal all transistor

**Terminal Circle Diameter:**

0.100 inches all transistor

**Field Force Effect Type:**

Electrostatic charge

**Features Provided:**

Hermetically sealed case and electrostatic sensitive

**Semiconductor Material:**

Silicon all transistor

**Voltage Rating In Volts Per Characteristic:**

35.0 drain to gate voltage all transistor

**Current Rating Per Characteristic:**

10.00 milliamperes source cutoff current minor all transistor

**Power Rating Per Characteristic:**

300.0 milliwatts small-signal input power, common-collector absolute all transistor

**Maximum Operating Tempurature Per Measurement Point:**

200.0 degrees celsius junction all transistor

**Terminal Type And Quantity:**

3 uninsulated wire lead all transistor

**Shelf Life:**

N/a

**Unit Of Measure:**

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**Demilitarization:**

Yes - demil/mli

**Fiig:**

A110a0